



HETERO JUNCTION FIELD EFFECT TRANSISTOR

NE3509M04

L TO S BAND LOW NOISE AMPLIFIER

N-CHANNEL HJ-FET

FEATURES

- Super low noise figure and high associated gain
NF = 0.4 dB TYP., $G_a = 17.5$ dB TYP. @ $f = 2$ GHz, $V_{DS} = 2$ V, $I_D = 10$ mA
- Flat-lead 4-pin thin-type super minimold (M04) package

APPLICATIONS

- Satellite radio (SDARS, DMB, etc.) antenna LNA
- GPS antenna LNA
- Low noise amplifier for microwave communication system

ORDERING INFORMATION

<R>

| Part Number | Order Number | Package | Quantity | Marking | Supplying Form |
|---------------|-----------------|--|-------------------|---------|--|
| NE3509M04 | NE3509M04-A | Flat-lead 4-pin thin-type super minimold (M04) (Pb-Free) | 50 pcs (Non reel) | V80 | • 8 mm wide embossed taping • Pin 1 (Source), Pin 2 (Drain) face the perforation side of the tape |
| NE3509M04-T2 | NE3509M04-T2-A | | 3 kpcs/reel | | |
| NE3509M04-T2B | NE3509M04-T2B-A | | 15 kpcs/reel | | |

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE3509M04-A

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

| Parameter | Symbol | Ratings | Unit |
|-------------------------|---------------------------|-------------|------------------|
| Drain to Source Voltage | V_{DS} | 4.0 | V |
| Gate to Source Voltage | V_{GS} | -3.0 | V |
| Drain Current | I_D | I_{DSS} | mA |
| Gate Current | I_G | 200 | μA |
| Total Power Dissipation | P_{tot} ^{Note} | 150 | mW |
| Channel Temperature | T_{ch} | +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

Note Mounted on $1.08 \text{ cm}^2 \times 1.0 \text{ mm}$ (t) glass epoxy PCB

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

RECOMMENDED OPERATING CONDITIONS (T_A = +25°C)

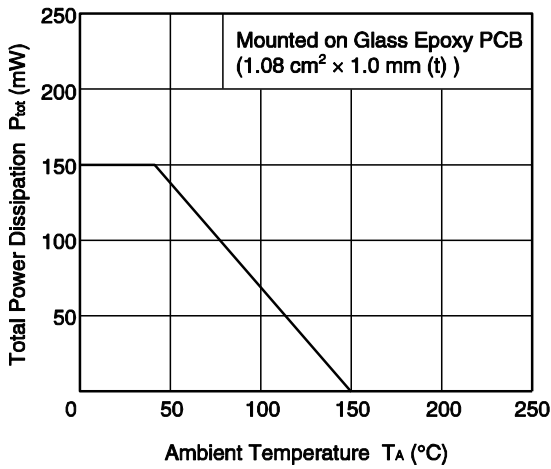
| Parameter | Symbol | MIN. | TYP. | MAX. | Unit |
|-------------------------|-----------------|------|------|------|------|
| Drain to Source Voltage | V _{DS} | – | 2 | 3 | V |
| Drain Current | I _D | – | 10 | 20 | mA |
| Input Power | P _{in} | – | – | 0 | dBm |

ELECTRICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

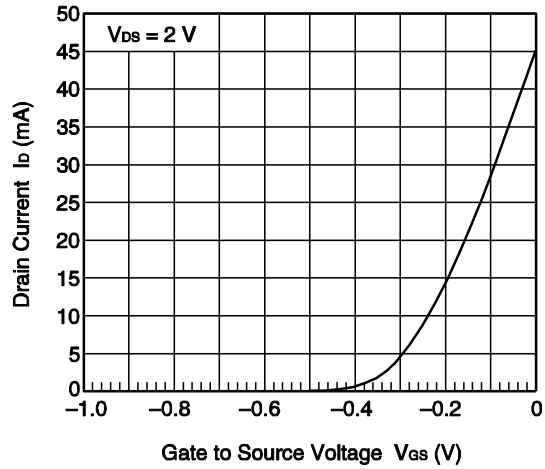
| Parameter | Symbol | Test Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------------------|-----------------------|--|-------|------|-------|------|
| Gate to Source Leak Current | I _{ISO} | V _{GS} = –3 V | – | 0.5 | 10 | μA |
| Saturated Drain Current | I _{DSS} | V _{DS} = 2 V, V _{GS} = 0 V | 30 | 45 | 60 | mA |
| Gate to Source Cutoff Voltage | V _{GS (off)} | V _{DS} = 2 V, I _D = 50 μA | –0.25 | –0.5 | –0.75 | V |
| Transconductance | g _m | V _{DS} = 2 V, I _D = 10 mA | 80 | – | – | mS |
| Noise Figure | NF | V _{DS} = 2 V, I _D = 10 mA, f = 2 GHz | – | 0.4 | 0.7 | dB |
| Associated Gain | G _a | | 16 | 17.5 | – | dB |
| Gain 1 dB Compression | P _{O (1 dB)} | V _{DS} = 2 V, I _D = 10 mA (Non-RF), f = 2 GHz | – | 11 | – | dBm |
| Output Power | | | | | | |

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

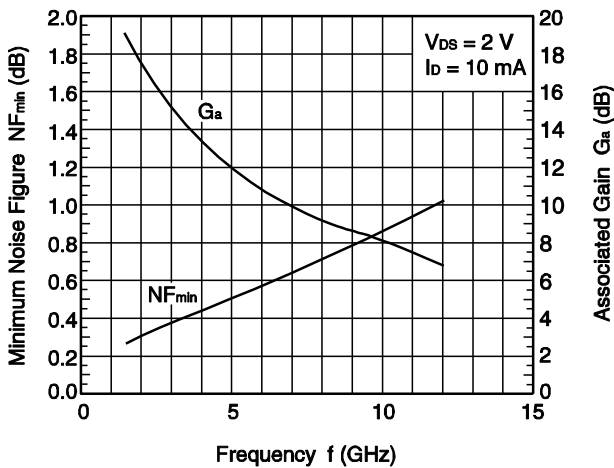
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



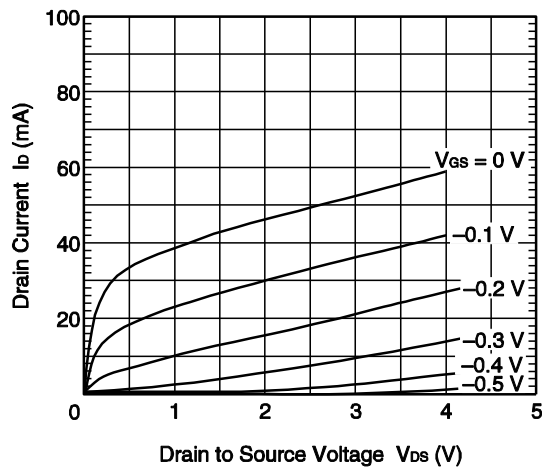
DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



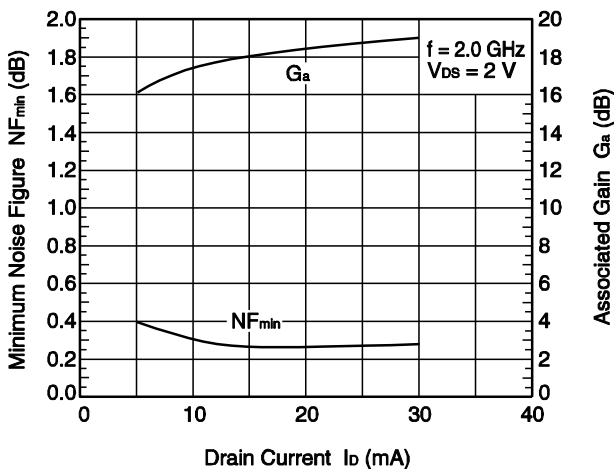
MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY



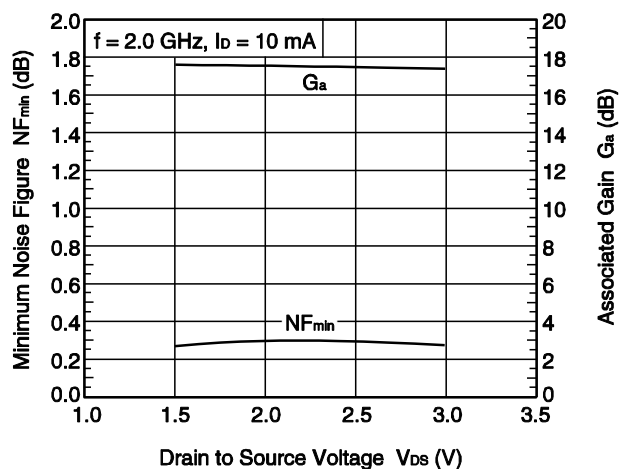
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT

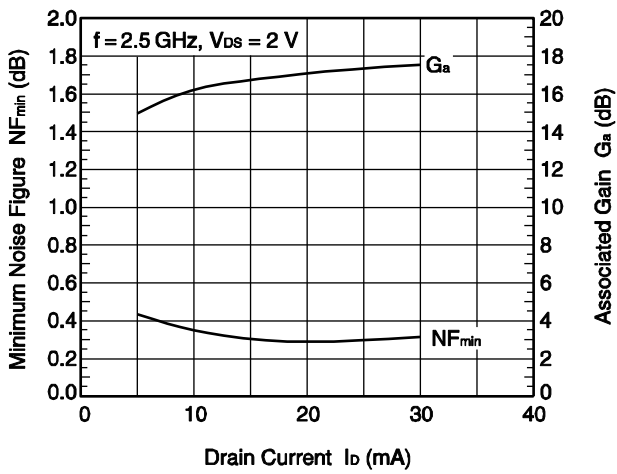


MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN TO SOURCE VOLTAGE

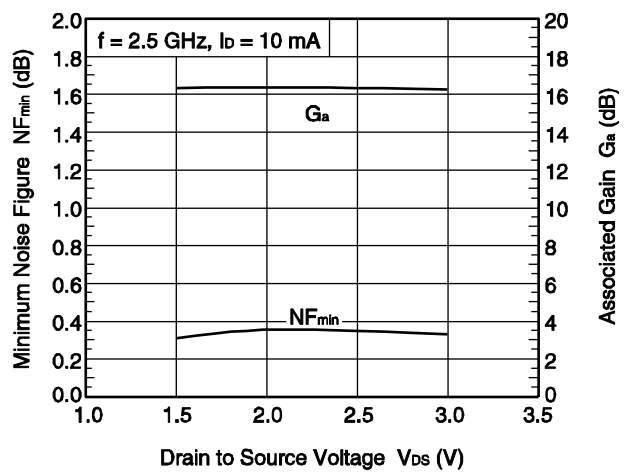


Remark The graphs indicate nominal characteristics.

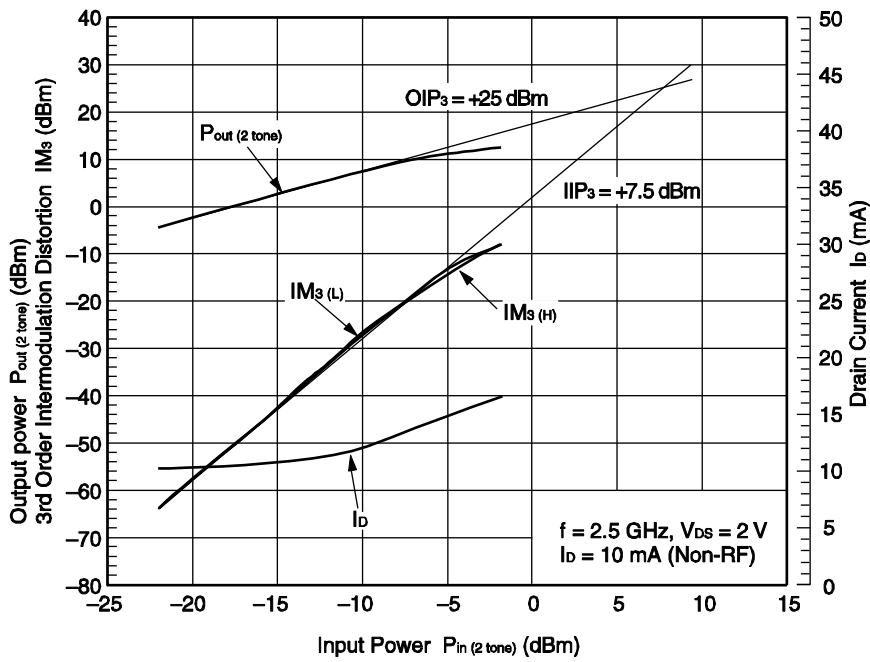
MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT



MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN TO SOURCE VOLTAGE



OUTPUT POWER, IM₃, DRAIN CURRENT vs. INPUT POWER



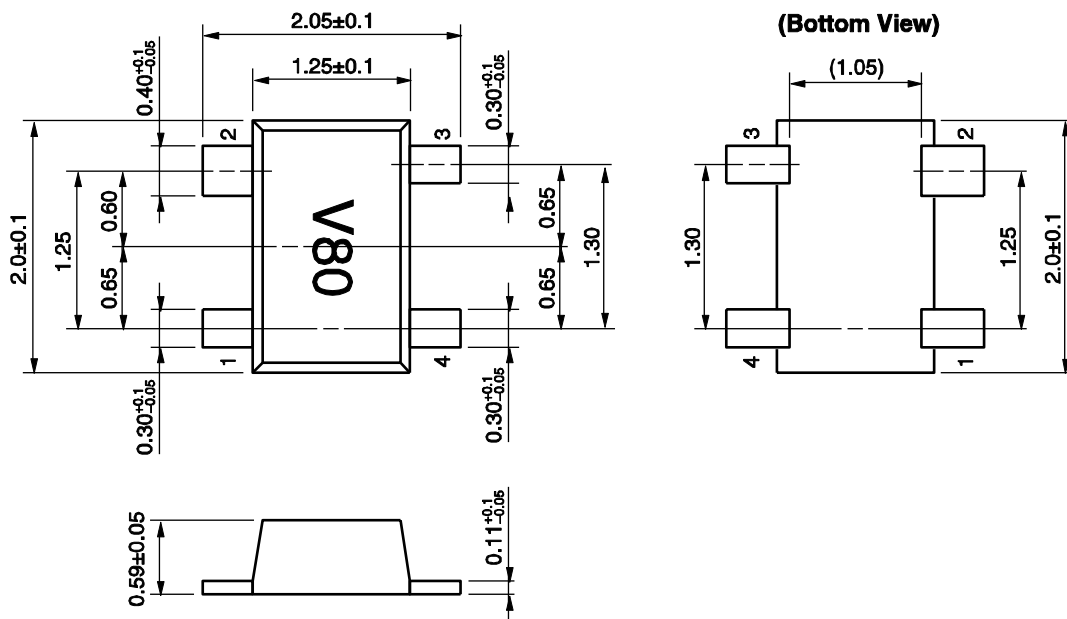
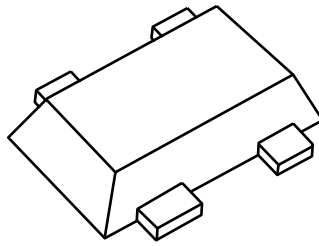
Remark The graphs indicate nominal characteristics.

S-PARAMETERS

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- [Click here to download S-parameters.](#)
- [RF and Microwave] ® [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)

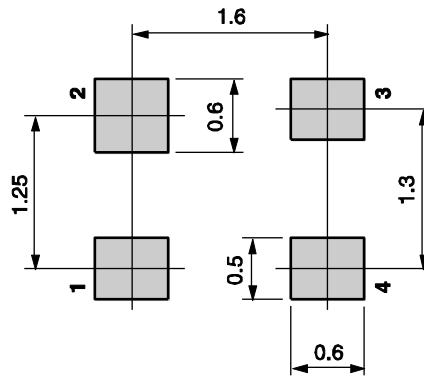


PIN CONNECTIONS

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

MOUNTING PAD DIMENSIONS (REFERENCE ONLY)

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

| Soldering Method | Soldering Conditions | Condition Symbol |
|------------------|---|------------------|
| Infrared Reflow | Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below | IR260 |
| Partial Heating | Peak temperature (terminal temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below | HS350 |

Caution Do not use different soldering methods together (except for partial heating).

| | | |
|-----------------------|----------------------|---|
| <p>Caution</p> | <p>GaAs Products</p> | <p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> • Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below. <ol style="list-style-type: none"> 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials. 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal. • Do not burn, destroy, cut, crush, or chemically dissolve the product. • Do not lick the product or in any way allow it to enter the mouth. |
|-----------------------|----------------------|---|



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
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Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.